

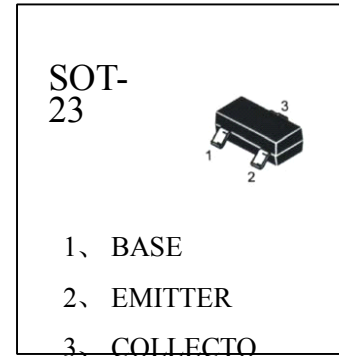
## SOT-23 Plastic –Encapsulate Transistors

### FEATURES

Power dissipation

**MARKING** : C1815=HF

**MAXIMUM RATINGS** (TA=25°C unless otherwise noted)



Symbol	Parameter	Value	Units
<b>VCBO</b>	Collector-Base Voltage	60	V
<b>VCEO</b>	Collector-Emitter Voltage	50	V
<b>VEBO</b>	Emitter-Base Voltage	5	V
<b>IC</b>	Collector Current -Continuous	150	mA
<b>PC</b>	Collector Power Dissipation	200	mW
<b>Tj</b>	Junction Temperature	125	°C
<b>Tstg</b>	Storage Temperature	-55-125	°C

### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
<b>Collector-base breakdown voltage</b>	V(BR)CBO	IC= 100uA, IE=0	60			V
<b>Collector-emitter breakdown voltage</b>	V(BR)CEO	IC= 0.1mA, IB=0	50			V
<b>Collector cut-off current</b>	ICBO	VCB=60 V, IE=0			0.1	A
<b>Collector cut-off current</b>	ICEO	VCE=50V, IB=0			0.1	uA
<b>Emitter cut-off current</b>	IEBO	VEB= 5V, IC=0			0.1	uA
<b>DC current gain</b>	hFE	VCE= 6V, IC= 2mA	130		400	
<b>Collector-emitter saturation voltage</b>	VCE(sat)	IC=100mA, IB= 10mA			0.25	V
<b>Base-emitter saturation voltage</b>	VBE(sat)	IC=100mA, IB= 10mA			1	V
<b>Transition frequency</b>	fT	VCE=10V, IC= 1mA, f=30MHz	80			MHz

### CLASSIFICATION OF hFE

Rank	L	H
<b>Range</b>	130-200	200-400

# Typical Characteristics

**C1815**

